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Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently amended) An electronic component built-in module, comprising:
 - a pair of opposed circuit substrates, in each of which a wiring pattern is formed on an insulating base material containing a resin;
 - an insulating layer that is placed between the pair of circuit substrates and contains an inorganic filler and a resin composition containing a thermosetting resin;
 - at least one electronic component that is embedded in the insulating layer; and
 - an inner via that is provided in the insulating layer so as to make an electrical connection between wiring patterns provided on different circuit substrates,wherein a glass transition temperature Tg1 of the resin composition contained in the insulating layer and a glass transition temperature Tg2 of the resin of the insulating base material included in each of the circuit substrates satisfy a relationship $Tg1 > Tg2$, and
 - wherein a difference between the glass transition temperature Tg1 and the glass transition temperature Tg2 is at least 10°C, and
 - wherein a rate of increase in amount of thermal expansion in a thickness direction of the insulating layer at a temperature from Tg2 to Tg1 is smaller than a rate of increase in amount of thermal expansion in a thickness direction of the insulating layer at a temperature higher than Tg1.
2. (canceled)
3. (original) The electronic component built-in module according to claim 1,
 - wherein a plurality of the insulating layers are provided.
4. (original) The electronic component built-in module according to claim 1,

wherein the insulating layer contains the inorganic filler in an amount of not less than 70% by weight and not more than 95% by weight.

5. (original) The electronic component built-in module according to claim 1,
wherein the inorganic filler contains at least one selected from the group consisting of:
 Al_2O_3 , MgO, BN, SiO_2 , SiC, Si_3N_4 , and AlN.
6. (original) The electronic component built-in module according to claim 1,
wherein the thermosetting resin contains at least one selected from the group consisting of: an epoxy resin, a phenol resin, and an isocyanate resin.
7. (original) The electronic component built-in module according to claim 1,
wherein the at least one electronic component comprises a semiconductor bare chip.
8. (original) The electronic component built-in module according to claim 1,
wherein the inner via is formed from a conductive resin composition.
9. (Currently amended) A method of manufacturing an electronic component built-in module, comprising the steps of:
 - (a) preparing at least two circuit substrates, in each of which a wiring pattern is formed on an insulating base material that contains a resin and has a glass transition temperature T_g2 , and mounting at least one electronic component on at least one of the circuit substrates;
 - (b) forming a sheet-like material in which a through-hole is formed in a predetermined region, using a mixture containing an inorganic filler and an uncured resin composition that contains at least a thermosetting resin and has a glass transition temperature T_g1 ;
 - (c) filling the through-hole with a conductive resin composition;
 - (d) placing the sheet-like material between the circuit substrates so that a face of each of the at least one of the circuit substrates, on which the at least one electronic component is mounted, is directed to a side of the sheet-like material, and embedding the at least one electronic component inside the sheet-like material by applying pressure in a thickness direction so that the sheet-like material and the circuit substrates are formed into one body; and

(e) forming an insulating layer by allowing the thermosetting resin contained in the sheet-like material to be cured,

wherein the glass transition temperature $Tg1$ and the glass transition temperature $Tg2$ satisfy a relationship $Tg1 > Tg2$, and

wherein a difference between the glass transition temperature $Tg1$ and the glass transition temperature $Tg2$ is at least 10°C , and

wherein a rate of increase in amount of thermal expansion in a thickness direction of the insulating layer at a temperature from $Tg2$ to $Tg1$ is smaller than a rate of increase in amount of thermal expansion in a thickness direction of the insulating layer at a temperature higher than $Tg1$.

10. (original) The method according to claim 9,

wherein in the step (d), an electronic component built-in layer, in which at least one electronic component is embedded in an insulating member containing a resin composition having the glass transition temperature $Tg1$, further is placed between the circuit substrates, and pressure is applied in the thickness direction.

11. (original) The method according to claim 9,

wherein in the step (d), at least two sheet-like materials, and an electronic component built-in layer in which at least one electronic component is embedded in an insulating member containing a resin composition having the glass transition temperature $Tg1$, are placed between the circuit substrates so that the sheet-like materials are in contact with the circuit substrates, and pressure is applied in the thickness direction.

12. (original) The method according to claim 10,

wherein a method of manufacturing the electronic component built-in layer comprises the steps of:

forming a wiring pattern on one face of a mold release carrier, and further mounting at least one electronic component thereon;

forming a sheet-like material in which a through-hole is formed in a predetermined region, using a mixture containing an inorganic filler and an uncured resin composition that contains at least a thermosetting resin and has the glass transition temperature T_g1 ;

filling the through-hole with a conductive resin composition;

laminating the mold release carrier on the sheet-like material so that the one face of the mold release carrier, on which the at least one electronic component is mounted, is directed to a side of the sheet-like material, and embedding the at least one electronic component inside the sheet-like material by applying pressure in a lamination direction; and

peeling the mold release carrier from the sheet-like material.

13. (original) The method according to claim 11,

wherein a method of manufacturing the electronic component built-in layer comprises the steps of:

forming a wiring pattern on one face of a mold release carrier, and further mounting at least one electronic component thereon;

forming a sheet-like material in which a through-hole is formed in a predetermined region, using a mixture containing an inorganic filler and an uncured resin composition that contains at least a thermosetting resin and has the glass transition temperature T_g1 ;

filling the through-hole with a conductive resin composition;

laminating the mold release carrier on the sheet-like material so that the one face of the mold release carrier, on which the at least one electronic component is mounted, is directed to a side of the sheet-like material, and embedding the at least one electronic component inside the sheet-like material by applying pressure in a lamination direction; and

peeling the mold release carrier from the sheet-like material.

14. (canceled)

15. (previously presented) The electronic component built-in module according to claim 1,

wherein the at least one electronic component embedded in the insulating layer is mounted on at least one of the pair of opposed circuit substrates.

16. (previously presented) The electronic component built-in module according to claim 1,
wherein at least one electronic component is mounted on each of the pair of circuit substrates, the circuit substrates being placed so that surfaces of the circuit substrates on which the electronic components are mounted face each other, the electronic components being housed in the insulating layer.
17. (previously presented) The electronic component built-in module according to claim 1,
wherein no electronic component is housed in the circuit substrates.